## Corrections and Additions for the $1^{\text {st }}$ Impression

Date: 16.9.2023
Author/Title: Forrest: Organic Electronics
ISBN: 9780198529729

|  | Page number | Line number | Incorrect content | Correction/instructions on how to correct |
| :---: | :---: | :---: | :---: | :---: |
| 1 | 22 | Column 2, para. <br> 3 , line 17 | tridentate molecule (have 3 ligands, or "teeth") | bidentate molecule (have 2 bonds, or "teeth" to each ligand) |
| 2 | 33 | Table 2.1 | Monoclinic | Change labels above both rectangles to " $\alpha, \gamma=90^{\circ}$ " |
| 3 | 35 | Column 2, $1^{\text {st }}$ paragraph, last line | "a•(b×c)" | " $\overline{\mathbf{a}} \cdot(\overline{\mathbf{b}} \times \overline{\mathbf{c}})$ " |
| 4 | 42 | Fig. 2.9, vertical axis label | "Energy/ hcR" | "Energy/ hcR ${ }_{\infty}$ " |
| 5 | 43 | Column 2, $2^{\text {nd }}$ line from bottom. | $"-\Delta \Phi(\mathbf{r}) "$ | $"-\nabla \Phi(\mathbf{r})$ " |
| 6 | 45 | Column 1, $1^{\text {st }}$ full para., line 7 | "a full electron charge" | "0.1q" |
| 7 | 76 | Figure 3.1 B | Diagram at far right shows " $\mathrm{S}=0$ " | Change to " $\mathrm{S}=1$ " |
| 8 | 79 | $\begin{array}{\|l\|} \hline \text { Column 2, Eq. } \\ 3.18 \\ \hline \end{array}$ | "me" | " $m_{N}$ " |


| 9 | 82 | Column 2, line 3 | "3.46" | "3.26" |
| :---: | :---: | :---: | :---: | :---: |
| 10 | 85 | Figure 3.11 caption |  | At end of caption, insert: "After Gribov \& Orville-Thomas, 1988" |
| 11 | 105 | Col. 1, starting 2 lines above Eq. 3.98 | "will decrease to $I(d)$ after travelling a distance, $x$ (cf Eq. 3.94): $I(d)=I(0) e^{-\alpha(v) x}$ | "will decrease to $I(x)$ after travelling a distance, $x$ (cf Eq. 3.94): $I(x)=I(0) e^{-\alpha(v) x}$, |
| 12 | 109 | Column 2, line 10 from bottom | "thermally assisted" | "thermally activated (or assisted)" |
| 13 | 156 | Col. 2, Eq. 3.255 | $\frac{L_{D}}{\tau_{r}}{ }^{2} \frac{\partial^{2} n(x)}{\partial x^{2}}-\frac{n(x)}{\tau_{r}}+\frac{I_{0} \alpha(\lambda)}{\cos \theta} \exp \left(-\frac{\alpha(\lambda) x}{\cos \theta}\right)=0$ | $\frac{L_{D}}{\tau_{D}} \frac{\partial^{2} n(x)}{\partial x^{2}}-\frac{n(x)}{\tau_{D}}+\frac{I_{0} \alpha(\lambda)}{\cos \theta} \exp \left(-\frac{\alpha(\lambda) x}{\cos \theta}\right)=0$ |
| 14 | 165 | Column 1, Prob. 13(b), line 4-6 | "Note that the absorption peaks at $<400 \mathrm{~nm}$ are in a different electronic manifold than at $>450 \mathrm{~nm}$." | Delete sentence |
| 15 | 165 | Column 1, Prob. 13(c), line 2 |  | Change "3.2" to "3.2 and m*=m" |
| 16 | 198 | In the line following Eq. 105 |  | Insert "where C is a density-dependent fitting parameter". |
| 17 | 218 | Col. 2, paragraph 1, line 2 | "Fig. 4.59a" | "Fig. 4.58a" |
| 18 | 225 | Eq. 4.175 | There are two instances where $A^{\prime}$ is found. | Replace with A (i.e remove ') |
| 19 | 249 | Col. 1, first line after Eq. 4.277 | " $W=x_{n}+x_{p}{ }^{\prime \prime}$ | " $W=x_{p}-x_{n} "$ |
| 20 | 256 | Col. 2, line 1 | "Fig. 4.103" | "Fig. 4.101" |
| 21 | 272 | Column 2, line 18 |  | After the sentence ending "inorganic layers, respectively)." Insert: "The foregoing treatment closely follows that of Renshaw and Forrest (2014)." |


| 22 | 282 | Prob. 3(a), line 2 | $\left\langle\epsilon_{\infty}\right\rangle=-\frac{\sigma^{2}}{k_{B} T}$ |
| :--- | :--- | :--- | :--- | :--- |$]$| Delete this expression |
| :--- |
| 23 |
| 243 |
| 201 |


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| 32 | 378 | Col. 2, $3^{\text {rd }}$ paragraph, line 7 | "particular spectrum, photo-" | "particular spectrum, radio-" |
| 33 | 386 | Col. 2, $2^{\text {nd }}$ full paragraph, line 3 | "Fig. 6.20a" | "Fig. 6.22a" |
| 34 | 421 | Column 2, line <br> 2, second <br> paragraph | "known as thermally assisted" | "known as thermally activated (or assisted)" |
| 35 | 476 | Figure 6.126 caption |  | At end of caption, insert: "Adapted from Barnes et al., 2003)" |
| 36 | 476 | Col. 2, line 1 | "lifetime" | "decay rate" |
| 37 | 476 | Col. 2, Eq. 6.111 | $F \frac{\tau}{\tau_{0}}$ | $P F \frac{\tau}{\tau_{0}}$ |
| 38 | 504 | Col. 1 paragraph 1 to Col. 2 paragraph 1. | Delete text starting with "Increasing the operating temperature..." to "thus yields the stretched exponential behavior of the luminance" | Insert: "Increasing the operating temperature can also accelerate aging. We assume that the probability for destroying an emitting molecule is thermally activated, i.e. the probability is: $P=\exp \left(-\Delta E_{A} / k_{B} T\right)$, where $\Delta E_{A}$ is the activation energy for the formation of non-radiative molecular species. Now the rate of defect formation can be obtained by solving: $\begin{equation*} \frac{d Q}{d t}=-\left(Q-N_{0}\right) / \tau \tag{6.123} \end{equation*}$ |


|  |  |  |  | Where $Q$ is the defect density, $N_{0}$ is the total number of emitting molecules at $t=0$, and $\tau$ is the time for defect formation, as defined in Eq. 6.121. Solving Eq. 6.123 yields an exponential decrease in increase in defect density with time: $Q(t)=N_{0}(1-\exp (-t / \tau))$, which is consistent with $Q(0)=0$ and $Q(\infty)=N_{0}$, i.e. all the emitting centers are eventually eliminated as defects. Now, as above, we assume that the defect formation rate is thermally activated such that: $\begin{equation*} \frac{1}{\tau}=k_{0} \exp \left(-\Delta E_{A} / k_{B} T\right) \tag{6.124} \end{equation*}$ <br> Equations 6.121 and 124 suggest that increasing $T$ will accelerate the degradation in luminance, $L(t)$. Then, combining 6.122 and 6.124 we arrive at a luminance lifetime at standard operating initial luminance and operating temperature, $T_{0}$, that can be related to accelerated by elevated test temperature, $T_{t s t}$, and initial luminance, $L_{0 t s t}$ : $\operatorname{LTx}\left(L_{0}, T_{0}\right)=L T x\left(L_{t s t}, T_{t s t}\right)\left[\frac{L_{0 t s t}}{L_{0}}\right]^{n} \exp \left(-\frac{\Delta E_{A}}{k_{B}}\left(\frac{1}{T_{t s t}}-\frac{1}{T_{0}}\right)\right)$ <br> (6.125) <br> This methodology is valid only if the test conditions allow for independent determination of lifetime due to temperature and luminance. Also, the temperature and initial luminance used in the accelerated aging tests must be kept sufficiently low so as not to introduce degradation processes that differ from those experienced under normal operating conditions. Note that a similar analysis also applies to organic detectors (see Sec. 7.8)." |
| :---: | :---: | :---: | :---: | :---: |
| 39 | 552 | Col. 2, line 2 | "emitting OLED, along" | "emitting OLED on a glass substrate, along" |
| 40 | 552 | Fig. P6.4 | Right axis label "cd/cm ${ }^{\text {" }}$ | Change to "cd/m" |
| 41 | 554 | Column 1, Prob. 6.9a, line 3 | $n_{\text {SiNx }}$ | $n_{\text {SiO2 }}$ |
| 42 | 554 | Column 1, Prob. 6.9a, line 6 | "into the glass substrate?" | "into the air? Assume $\lambda=550 \mathrm{~nm}$." |
| 43 | 554 | Column 1, Prob. <br> 13, line 2-3 | "30, 50, and 100" | "30, and 50" |


| 44 | 555 | Column 2, after reference "Barnes, W. L. 1998..." |  | Insert a new reference: <br> "Barnes, W. L., Dereux, A. \& Ebbesen, T. W. 2003. Nature, 424, 824." |
| :---: | :---: | :---: | :---: | :---: |
| 45 | 566 | Column 2, line 5 | "Appl. Phys., 92" | Change to "Appl. Phys. Lett., 92" |
| 46 | 570 | Column 2, line 7 after Eq. 7.3 | "equal to the total number of photons incident to the electrons generated" | "equal to the ratio of the total number of electrons generated to the photons incident" |
| 47 | 573 | Col. 2 line just prior to Eq. 7.24 | "Eq. 7.3" | "Eq. 7.14" |
| 48 | 573 | Col. 2 line 5 following Eq. 7.24 | "that reach the active" | "that generate charge in the active" |
| 49 | 577 | Col. 2, Eq. 7.48 | $" \eta_{\text {ext }}=\eta_{A} \eta_{\text {int }}=$ " | $" \eta_{\text {int }}=$ " |
| 50 | 580 | Fig. 7.9 | One too many charge recomb. zones in the figure | Replace figure with the one attached |
| 51 | 580 | Col. 1, para. 1, line 9 | "is similar to" | "differs from" |
| 52 | 586 | Col. 2, line 1 | ", or less than" | Delete text |


| 53 | $\begin{aligned} & \text { 587, Eq. } \\ & 7.65 \end{aligned}$ | Col. 2, Eq. 7.65 |  | Replace Eq. 7.65 with " $\Delta f=\frac{1}{2 \pi}\left(\frac{1}{\tau_{E D}+t_{t r}+\tau_{R C}}\right)$ " |
| :---: | :---: | :---: | :---: | :---: |
| 54 | 605 | Fig. 7.37 | The insets labelled "Porphyrin tapes", "Squaraines" and "PDDTT" need to be corrected | See attached. |
| 55 | 608 | Col. 1, line 1-2 | Delete: "All device responses are limited by the hole transit time across the donor layers" | Insert: "While the frequency response of these devices is attributed to the limited hole mobilities in the donors, it may also be due, in part, to slow exciton diffusion to the HJ from their point of generation in the donor and acceptor layers." |
| 56 | 613 | Line immediately above Eq. 7.114 | "solutions to Eq. 7.112 yield" | "solutions to Eq. 7.112 for s-states yield" |
| 57 | 632 | Equation 7.138 | " $5.52 \times 10^{-5 "}$ | Change to " $5.52 \times 10^{-5} \mathrm{sr}$ " |
| 58 | 635 | Col. 1, line 3 | " $\eta_{\text {EL }}$ " | " $\eta_{C T}{ }^{\prime \prime}$ |
| 59 | 699 | Col. 1, Caption Fig. 7.158 | "Modular, axisymmetric architecture commonly used in the design of high performance donors and nonfullerene acceptors. Here, "d" and "a" represent donor and acceptor units, and " $\pi$ " is a conjugated bridge between units." | "Modular, axisymmetric architecture commonly used in the design of high performance non-fullerene acceptors. Here, "d" and "a" represent donor and acceptor units, and " $\pi$ " is a conjugated bridge between units. Donors have a similar structure but with d and a moieties switched." |


| 60 | 730 | Col. 1, para. 1, lines 2-13 | "When an electron from an adjacent acceptor layer is at distance $r$ from a neutral Ag NP metal sphere, it is attracted by its mirror image with a force of $q^{2} /\left(4 \pi \varepsilon_{r} \varepsilon_{0} r^{2}\right)$. Once the electron binds to the sphere, the NP is negatively charged, and subsequently attracts a hole from the adjacent donor layer with the same force. The electron and hole recombine, and the process begins once more starting with the neutral NP. The binding energy of an electron to the NP is $E_{B}=q^{2} /\left(8 \pi \varepsilon_{r} \varepsilon_{0} r\right)$. At room temperature, and at a distance, $r=4 \mathrm{~nm}, E_{B}=2.4 k_{B} T$." | When an electron from an adjacent acceptor layer is at distance $r \gg R$ from a neutral Ag NP metal sphere of radius $R$, it is attracted by its mirror image with a force of $-\frac{q^{2}}{4 \pi \epsilon_{0} \epsilon_{r}} \frac{R}{r^{3}}$. Once the electron binds to the sphere, the NP is negatively charged, and subsequently attracts a hole from the adjacent donor layer with the same force. The electron and hole recombine, and the process begins once more starting with the neutral NP. The attractive energy of an electron to the NP is $E_{B}=-\frac{q^{2}}{8 \pi \epsilon_{0} \epsilon_{r}} \frac{R}{\left(r^{2}-R^{2}\right)}$. At room temperature, a charge at a distance, $r=4 \mathrm{~nm}$, for a sphere of radius $2 \mathrm{~nm}, E_{B} \approx-1.5 k_{B} T$. |
| :---: | :---: | :---: | :---: | :---: |
| 61 | 761 | Column 2 | Insert sentence immediately following Eq. (7.216) | "Note that this expression is valid only if the accelerated aging by intensity is independent of thermal acceleration." |
| 62 | 777 | Col. 2, Eq. 7.220 + following 2 lines | $" \Delta P_{\text {loss }}=I^{2} R_{\text {ser }}$ <br> (7.220) <br> Thus, series-connected cells in modules are preferred over parallel-connected cells to minimize losses" | " $\Delta P_{\text {loss }}=I^{2} R_{\text {ser }}=V^{2} / R_{\text {ser }}$ <br> Thus, series-connected cells in modules are preferred over parallelconnected cells to minimize current losses" |
| 63 | 786 | Prob. 9(c), line 2 | "at SRC" | delete |
| 64 | 795 | Column 2, first reference | Delete "High efficiency semi-transparent organic photovoltaics. $46^{\text {th }}$ IEEE PVSC, June 16-21, 2019. Chicago, IL. Paper 484" | Insert "2019. Enhanced light utilization in semitransparent organic photovoltaics using an optical outcoupling architecture. Adv. Mater., 31, 1903173." |
| 65 | 840 | Fig. 8.53b | " 0.0 " on $x$-axis | Change to "1" |
| 66 | 840 | Fig. 8.53c | Right axis, second number from top is " $10^{-8 \prime}$ " | Change to " $10^{-7 \prime \prime}$ |
| 67 | 907 | Prob. 11 | Replace parts (a) and (b) with new text. | "(a) How well does the gate leakage for Fig. 8.98, option B fit to Frenkel-Poole its dominant source for an 3.6 nm thick $\mathrm{AlO}_{x}$ gate insulator coated by a 2.1 nm thick SAM, with $\varepsilon_{\mathrm{r}}=9.8$ and 3.5 , respectively (cf Fig. 8.96). <br> (b) From the best fits in (a), what is the Frenkel-Poole prefactor, A, in Eq. 7.110?" |

